

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Chandra V. Mouli
App. No.	:	Not Yet Known
Filed	:	Herewith
For	:	SOI CMOS DEVICE WITH REDUCED DIBL
Examiner	:	Not Yet Known
Group Art Unit	:	Not Yet Known

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing seventeen (17) references that are also enclosed. This Information Disclosure Statement is being filed within three months of the filing date of this application or upon filing if this is a CPA or RCE, and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,
KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 3/15/04

By: 

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.261A	APPLICATION NO. Not Yet Known
	APPLICANT Chandra V. Mouli	
	FILING DATE Herewith	GROUP Not Yet Known

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	4,199,773	04/22/80	Goodman et al.			
	2	5,024,965	06/18/91	Chang et al.			
	3	5,164,805	11/17/92	Lee			
	4	5,166,765	11/24/92	Lee et al.			
	5	5,231,045	07/27/93	Miura et al.			
	6	5,315,144	05/24/94	Cherne			
	7	5,501,993	03/26/96	Borland			
	8	5,599,728	02/04/97	Hu et al.			
	9	5,614,433	03/25/97	Mandelman			
	10	5,942,781	08/24/99	Burr. et al.			
	11	6,037,617	03/14/00	Kumagai			
	12	6,268,630	07/31/01	Schwank et al.			
	13	6,503,783	01/07/03	Mouli			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

	14	Park et al., "Dopant Redistribution in SOI during RTA: A Study on Doping in Scaled-down Si Layers", <i>IEEE</i> , 1999, pp 14.2.1 through 14.2.4.
	15	"A.1.3.2 Spurious Effects in Sub-Micron MOSFETs", http://www.iue.tuwien.ac.at/diss/schrom/diss/node90.html
	16	"2.7.2 Threshold Control", http://www.iue.tuwien.ac.at/diss/schrom/diss/node26.html
	17	"Random discrete dopant fluctuation; Ultra-thin channel SOI", http://www.research.ibm.com/0.1um/pwong.html

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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	